



# RF Power LDMOS Transistor

## N-Channel Enhancement-Mode Lateral MOSFET

This 50 W RF power LDMOS transistor is designed for cellular base station applications covering the frequency range of 1805 to 1995 MHz.

### 1800 MHz

- Typical single-carrier W-CDMA performance:  $V_{DD} = 28$  Vdc,  $I_{DQ} = 1400$  mA,  $P_{out} = 50$  W Avg., input signal PAR = 9.9 dB @ 0.01% probability on CCDF.

Frequency	$G_{ps}$ (dB)	$\eta_D$ (%)	Output PAR (dB)	ACPR (dBc)	IRL (dB)
1805 MHz	18.9	30.1	7.7	-35.8	-17
1840 MHz	19.3	30.0	7.6	-36.5	-19
1880 MHz	19.2	30.3	7.5	-36.8	-9

### 1900 MHz

- Typical single-carrier W-CDMA performance:  $V_{DD} = 28$  Vdc,  $I_{DQ} = 1400$  mA,  $P_{out} = 50$  W Avg., input signal PAR = 9.9 dB @ 0.01% probability on CCDF.

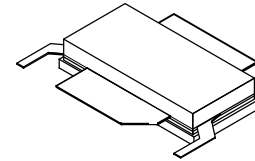
Frequency	$G_{ps}$ (dB)	$\eta_D$ (%)	Output PAR (dB)	ACPR (dBc)	IRL (dB)
1930 MHz	19.1	29.2	7.6	-35.1	-23
1960 MHz	19.4	29.9	7.6	-36.0	-15
1995 MHz	19.6	31.0	7.4	-35.7	-10

### Features

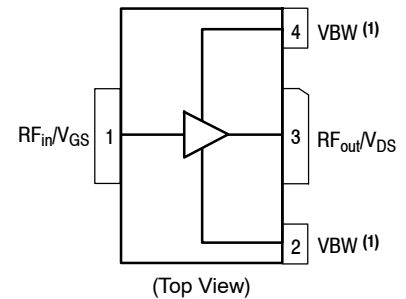
- Greater negative gate-source voltage range for improved Class C operation
- Designed for digital predistortion error correction systems
- Optimized for Doherty applications

## A2T18S260-12SR3

**1805-1995 MHz, 50 W AVG., 28 V AIRFAST RF POWER LDMOS TRANSISTOR**



NI-780S-2L2L



**Figure 1. Pin Connections**

- Device cannot operate with  $V_{DD}$  current supplied through pin 2 and pin 4.

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +65	Vdc
Gate-Source Voltage	$V_{GS}$	-6.0, +10	Vdc
Operating Voltage	$V_{DD}$	32, +0	Vdc
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Case Operating Temperature Range	$T_C$	-40 to +150	°C
Operating Junction Temperature Range (1,2)	$T_J$	-40 to +225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 89°C, 50 W CW, 28 Vdc, $I_{DQ} = 1400$ mA, 1840 MHz	$R_{\theta JC}$	0.36	°C/W

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	2
Machine Model (per EIA/JESD22-A115)	B
Charge Device Model (per JESD22-C101)	IV

**Table 4. Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**Off Characteristics**

Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 65$ Vdc, $V_{GS} = 0$ Vdc)	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 32$ Vdc, $V_{GS} = 0$ Vdc)	$I_{DSS}$	—	—	1	$\mu\text{Adc}$
Gate-Source Leakage Current ( $V_{GS} = 5$ Vdc, $V_{DS} = 0$ Vdc)	$I_{GSS}$	—	—	1	$\mu\text{Adc}$

**On Characteristics**

Gate Threshold Voltage ( $V_{DS} = 10$ Vdc, $I_D = 270$ $\mu\text{Adc}$ )	$V_{GS(th)}$	1.4	1.8	2.2	Vdc
Gate Quiescent Voltage ( $V_{DD} = 28$ Vdc, $I_D = 1400$ mAdc, Measured in Functional Test)	$V_{GS(Q)}$	2.1	2.5	2.9	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10$ Vdc, $I_D = 2.7$ Adc)	$V_{DS(on)}$	0.05	0.15	0.25	Vdc

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.nxp.com/RF/calculators>.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.nxp.com/RF> and search for AN1955.

(continued)

**Table 4. Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Functional Tests</b> <sup>(1)</sup> (In NXP Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$ , $I_{DQ} = 1400\text{ mA}$ , $P_{out} = 50\text{ W Avg.}$ , $f = 1805\text{ MHz}$ , Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 9.9 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset.					
Power Gain	$G_{ps}$	17.6	18.9	20.6	dB
Drain Efficiency	$\eta_D$	27.5	30.1	—	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	7.3	7.7	—	dB
Adjacent Channel Power Ratio	ACPR	—	-35.8	-32	dBc
Input Return Loss	IRL	—	-17	-8	dB

**Load Mismatch** (In NXP Test Fixture, 50 ohm system)  $I_{DQ} = 1400\text{ mA}$ ,  $f = 1840\text{ MHz}$ ,  $12\ \mu\text{sec(on)}$ , 10% Duty Cycle

VSWR 10:1 at 32 Vdc, 416 W Pulsed CW Output Power (3 dB Input Overdrive from 250 W Pulsed CW Rated Power)	No Device Degradation
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**Typical Performance** (In NXP Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 1400\text{ mA}$ , 1805–1880 MHz Bandwidth

$P_{out}$ @ 1 dB Compression Point, CW	P1dB	—	257	—	W
$P_{out}$ @ 3 dB Compression Point <sup>(2)</sup>	P3dB	—	323	—	W
AM/PM (Maximum value measured at the P3dB compression point across the 1805–1880 MHz bandwidth)	$\Phi$	—	-17.4	—	°
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	VBW <sub>res</sub>	—	85	—	MHz
Gain Flatness in 75 MHz Bandwidth @ $P_{out} = 50\text{ W Avg.}$	$G_F$	—	0.2	—	dB
Gain Variation over Temperature (-30°C to +85°C)	$\Delta G$	—	0.011	—	dB/°C
Output Power Variation over Temperature (-30°C to +85°C)	$\Delta P1dB$	—	0.008	—	dB/°C

**Table 5. Ordering Information**

Device	Tape and Reel Information	Package
A2T18S260-12SR3	R3 Suffix = 250 Units, 44 mm Tape Width, 13-inch Reel	NI-780S-2L2L

- Part internally matched both on input and output.
- P3dB =  $P_{avg} + 7.0\text{ dB}$  where  $P_{avg}$  is the average output power measured using an unclipped W-CDMA single-carrier input signal where output PAR is compressed to 7.0 dB @ 0.01% probability on CCDF.

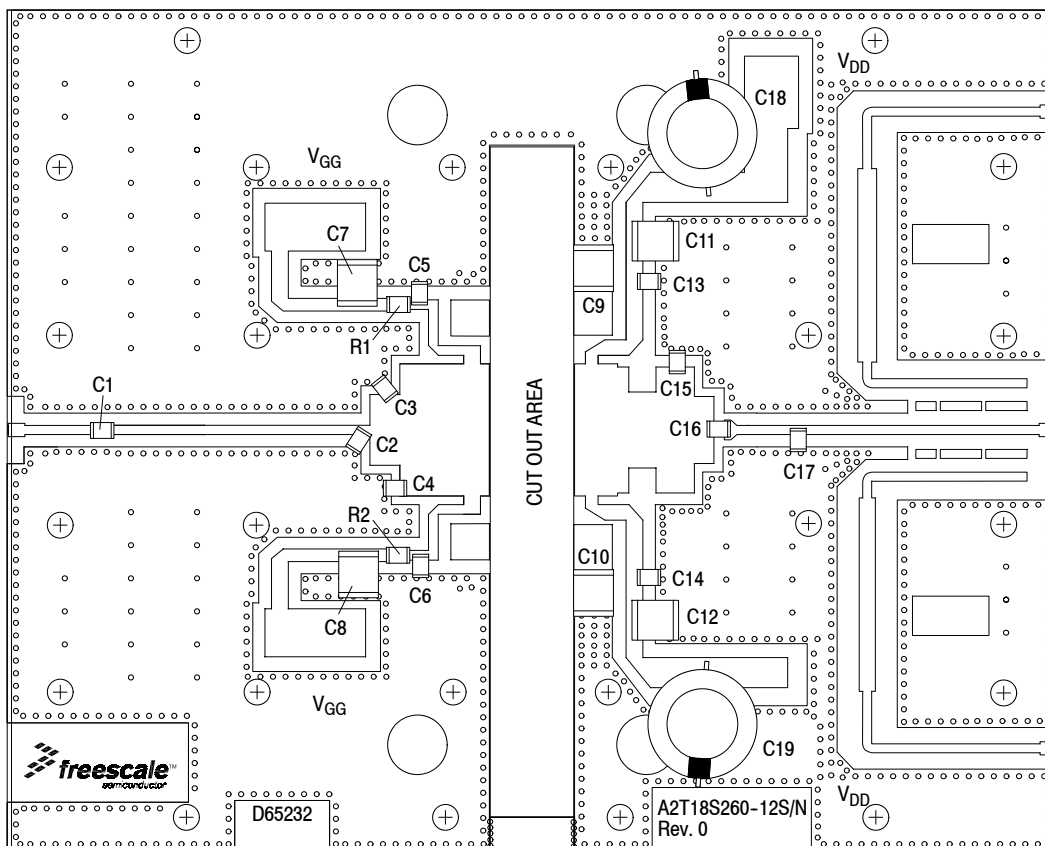


Figure 2. A2T18S260-12SR3 Test Circuit Component Layout

Table 6. A2T18S260-12SR3 Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1	5.1 pF Chip Capacitor	ATC600F5R1BT250T	ATC
C2, C3	1.1 pF Chip Capacitors	ATC600F1R1BT250T	ATC
C4	0.7 pF Chip Capacitor	ATC600F0R7BT250T	ATC
C5, C6, C13, C14, C16	15 pF Chip Capacitors	ATC600F150FT250T	ATC
C7, C8, C9, C10, C11, C12	10 $\mu$ F Chip Capacitors	C5750X7S2A106M230KB	TDK
C15	0.5 pF Chip Capacitor	ATC600F0R5BT250T	ATC
C17	0.2 pF Chip Capacitor	ATC600F0R2BT250T	ATC
C18, C19	470 $\mu$ F, 63 V Electrolytic Capacitors	MCGPR63V477M13X26-RH	Multicomp
R1, R2	3.9 $\Omega$ , 1/4 W Chip Resistors	CRCW12063R90FKEA	Vishay
PCB	Rogers RO4350B, 0.020", $\epsilon_r = 3.66$	D65232	MTL

### TYPICAL CHARACTERISTICS — 1805–1880 MHz

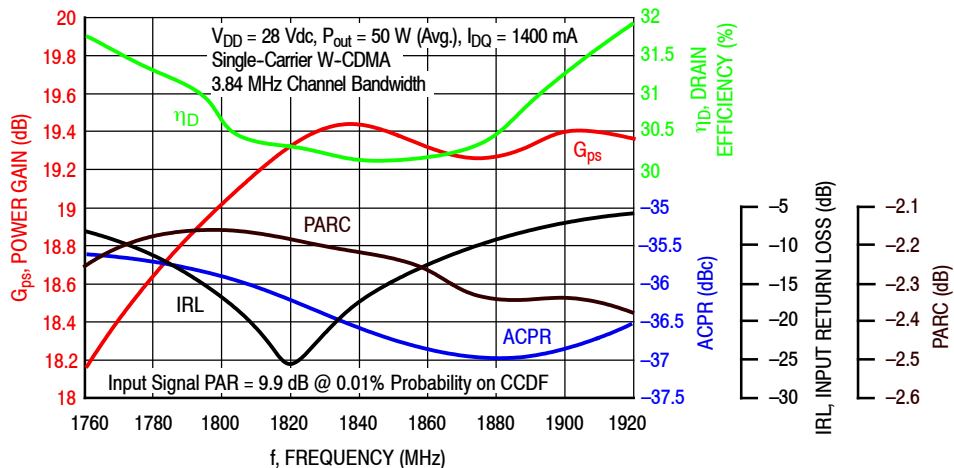


Figure 3. Single-Carrier Output Peak-to-Average Ratio Compression (PARC) Broadband Performance @  $P_{out} = 50$  Watts Avg.

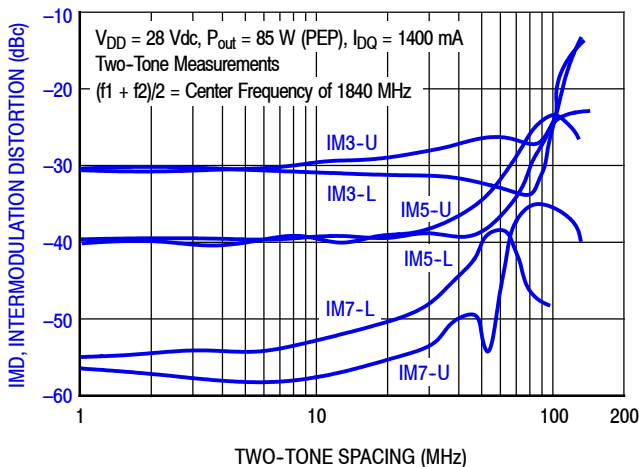


Figure 4. Intermodulation Distortion Products versus Two-Tone Spacing

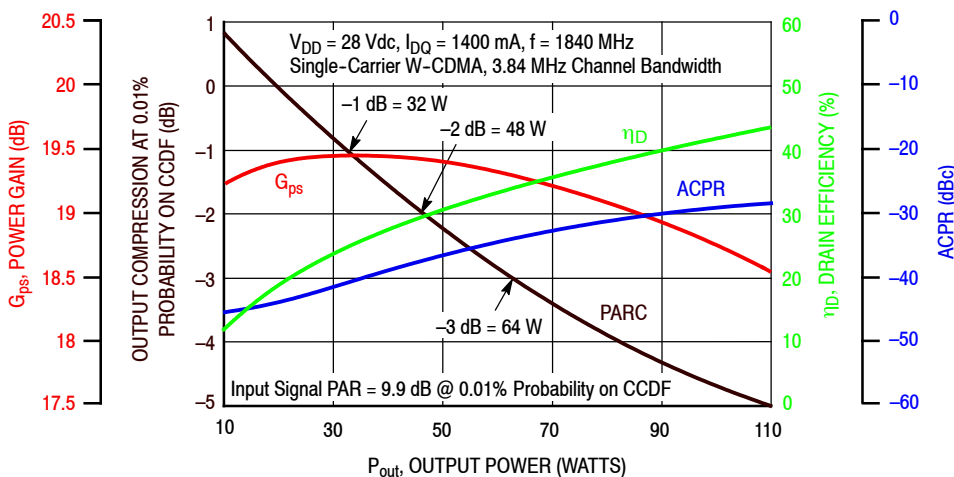


Figure 5. Output Peak-to-Average Ratio Compression (PARC) versus Output Power

TYPICAL CHARACTERISTICS — 1805–1880 MHz

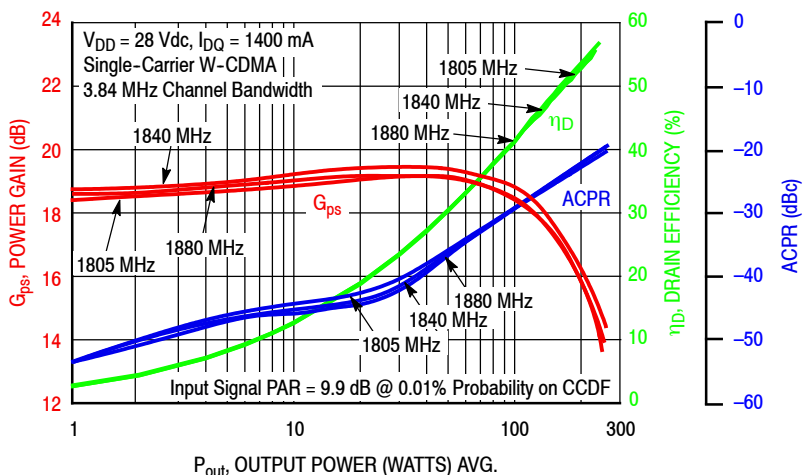


Figure 6. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power

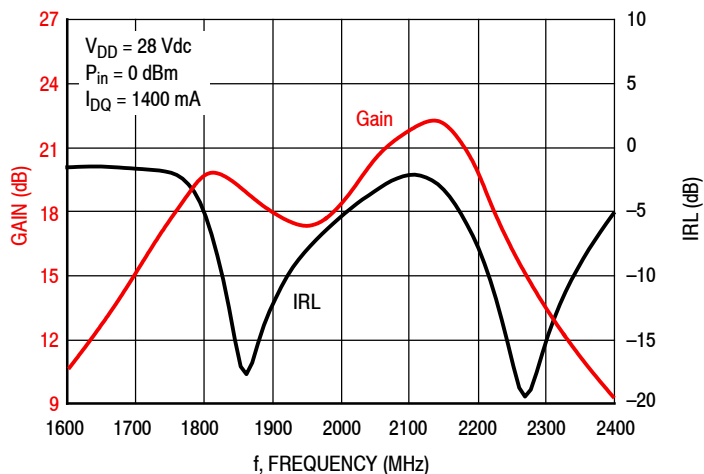


Figure 7. Broadband Frequency Response

**Table 7. Load Pull Performance — Maximum Power Tuning**

$V_{DD} = 28$  Vdc,  $I_{DQ} = 1390$  mA, Pulsed CW, 10  $\mu$ sec(on), 10% Duty Cycle

f (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{in}$ ( $\Omega$ )	Max Output Power					
			P1dB					
			$Z_{load}^{(1)}$ ( $\Omega$ )	Gain (dB)	(dBm)	(W)	$\eta_D$ (%)	AM/PM ( $^\circ$ )
1805	0.74 – j2.37	0.61 + j2.21	1.14 – j2.05	19.1	54.6	291	56.1	–13
1840	0.85 – j2.48	0.77 + j2.39	1.15 – j2.10	19.4	54.6	287	56.4	–14
1880	1.15 – j2.87	1.06 + j2.71	1.14 – j2.34	19.3	54.7	293	57.0	–15

f (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{in}$ ( $\Omega$ )	Max Output Power					
			P3dB					
			$Z_{load}^{(2)}$ ( $\Omega$ )	Gain (dB)	(dBm)	(W)	$\eta_D$ (%)	AM/PM ( $^\circ$ )
1805	0.74 – j2.37	0.57 + j2.27	1.19 – j2.21	17.0	55.5	357	59.9	–17
1840	0.85 – j2.48	0.74 + j2.46	1.18 – j2.37	17.0	55.4	350	58.6	–18
1880	1.15 – j2.87	1.03 + j2.82	1.21 – j2.54	17.1	55.5	356	59.5	–20

(1) Load impedance for optimum P1dB power.

(2) Load impedance for optimum P3dB power.

$Z_{source}$  = Measured impedance presented to the input of the device at the package reference plane.

$Z_{in}$  = Impedance as measured from gate contact to ground.

$Z_{load}$  = Measured impedance presented to the output of the device at the package reference plane.

**Table 8. Load Pull Performance — Maximum Efficiency Tuning**

$V_{DD} = 28$  Vdc,  $I_{DQ} = 1390$  mA, Pulsed CW, 10  $\mu$ sec(on), 10% Duty Cycle

f (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{in}$ ( $\Omega$ )	Max Drain Efficiency					
			P1dB					
			$Z_{load}^{(1)}$ ( $\Omega$ )	Gain (dB)	(dBm)	(W)	$\eta_D$ (%)	AM/PM ( $^\circ$ )
1805	0.74 – j2.37	0.65 + j2.31	2.76 – j0.95	21.9	52.5	178	67.3	–17
1840	0.85 – j2.48	0.80 + j2.46	1.98 – j1.36	21.5	53.3	216	65.2	–18
1880	1.15 – j2.87	1.12 + j2.80	1.90 – j1.31	21.7	53.2	207	67.3	–19

f (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{in}$ ( $\Omega$ )	Max Drain Efficiency					
			P3dB					
			$Z_{load}^{(2)}$ ( $\Omega$ )	Gain (dB)	(dBm)	(W)	$\eta_D$ (%)	AM/PM ( $^\circ$ )
1805	0.74 – j2.37	0.61 + j2.32	2.43 – j1.67	19.2	54.2	265	70.2	–21
1840	0.85 – j2.48	0.79 + j2.51	2.28 – j1.49	19.4	54.0	250	68.9	–24
1880	1.15 – j2.87	1.07 + j2.86	1.94 – j1.72	19.2	54.5	279	70.6	–24

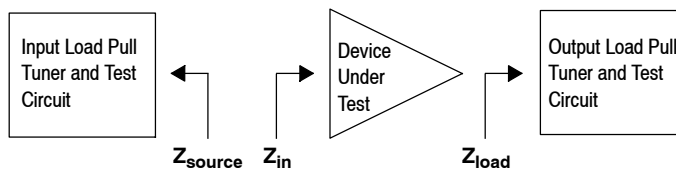
(1) Load impedance for optimum P1dB efficiency.

(2) Load impedance for optimum P3dB efficiency.

$Z_{source}$  = Measured impedance presented to the input of the device at the package reference plane.

$Z_{in}$  = Impedance as measured from gate contact to ground.

$Z_{load}$  = Measured impedance presented to the output of the device at the package reference plane.



## P1dB - TYPICAL LOAD PULL CONTOURS — 1840 MHz

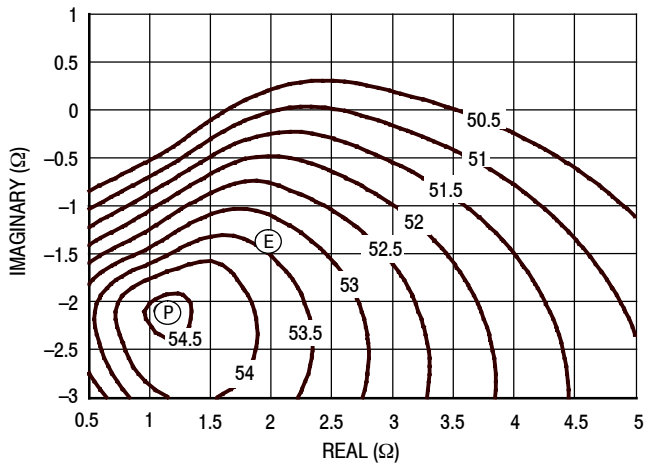


Figure 8. P1dB Load Pull Output Power Contours (dBm)

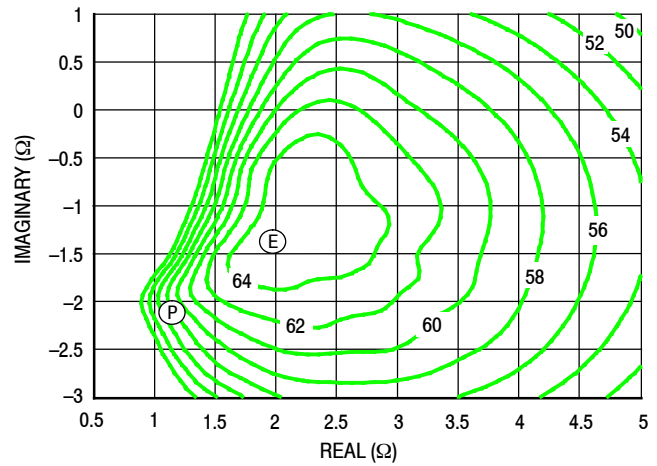


Figure 9. P1dB Load Pull Efficiency Contours (%)

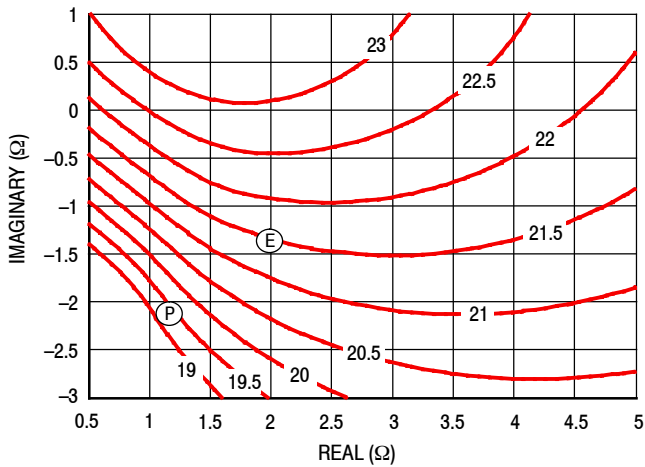


Figure 10. P1dB Load Pull Gain Contours (dB)

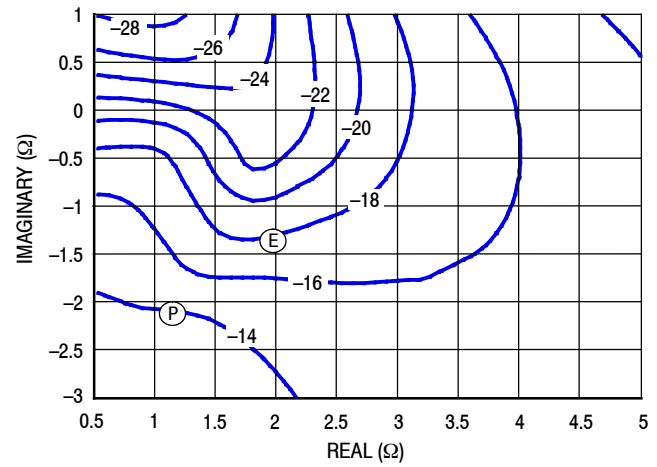


Figure 11. P1dB Load Pull AM/PM Contours (°)

**NOTE:** (P) = Maximum Output Power  
(E) = Maximum Drain Efficiency

- Gain
- Drain Efficiency
- Linearity
- Output Power



### P3dB – TYPICAL LOAD PULL CONTOURS — 1840 MHz

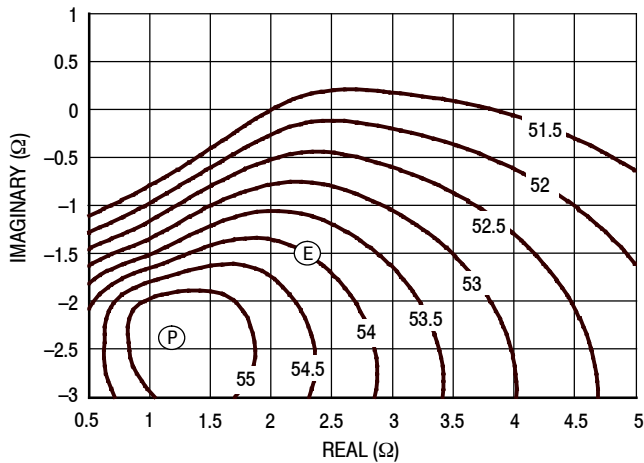


Figure 12. P3dB Load Pull Output Power Contours (dBm)

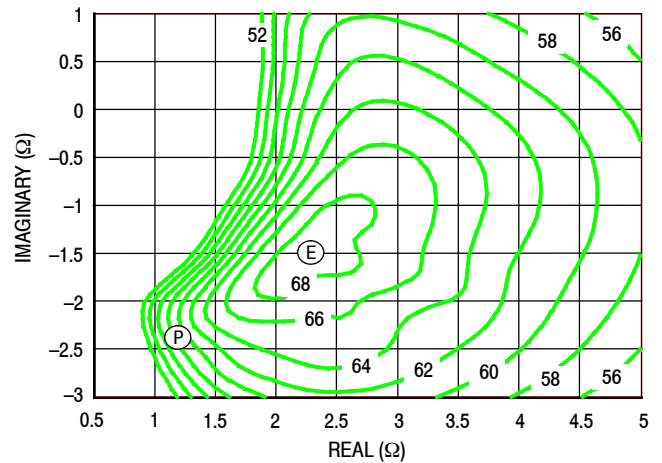


Figure 13. P3dB Load Pull Efficiency Contours (%)

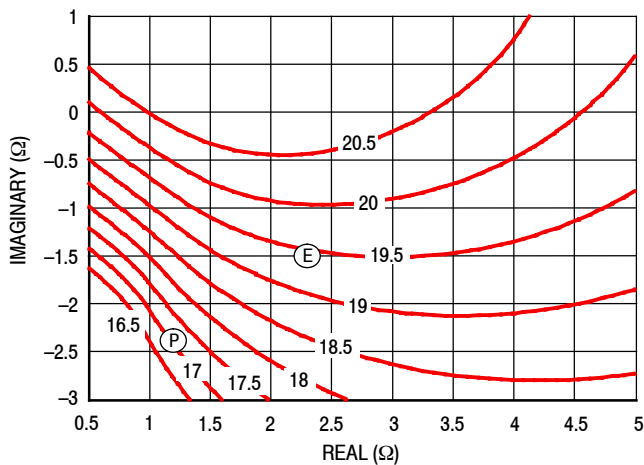


Figure 14. P3dB Load Pull Gain Contours (dB)

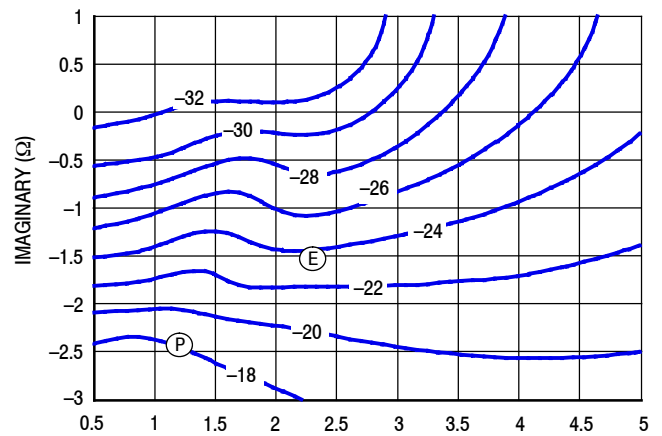


Figure 15. P3dB Load Pull AM/PM Contours (°)

**NOTE:** (P) = Maximum Output Power

(E) = Maximum Drain Efficiency

- Gain
- Drain Efficiency
- Linearity
- Output Power

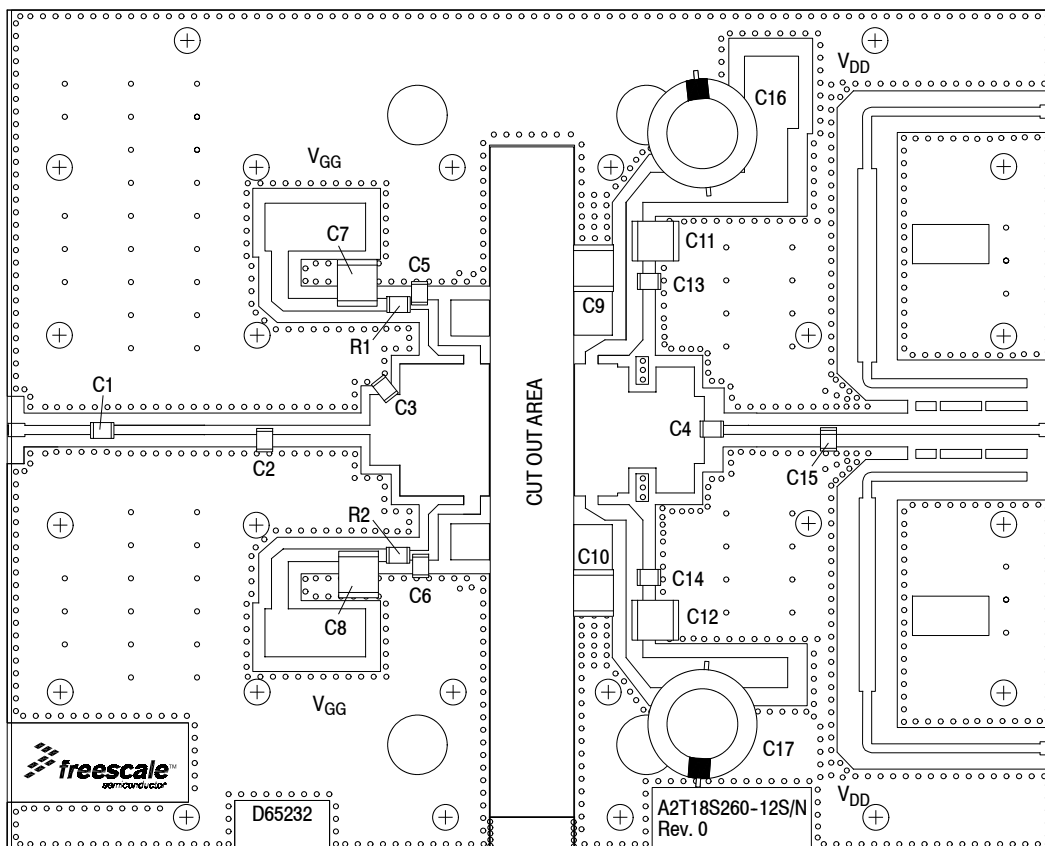


Figure 16. A2T18S260-12SR3 Test Circuit Component Layout — 1930–1995 MHz

Table 9. A2T18S260-12SR3 Test Circuit Component Designations and Values — 1930–1995 MHz

Part	Description	Part Number	Manufacturer
C1, C5, C6, C13, C14	15 pF Chip Capacitors	ATC600F150JT500XT	ATC
C2	0.6 pF Chip Capacitor	ATC600F0R6BT500XT	ATC
C3	0.7 pF Chip Capacitor	ATC600F0R7BT500XT	ATC
C4	6.8 pF Chip Capacitor	ATC600F6R8BT500XT	ATC
C7, C8, C9, C10, C11, C12	10 $\mu$ F Chip Capacitors	C5750X7S2A106M230KB	TDK
C15	0.1 pF Chip Capacitor	ATC600F0R1BT500XT	ATC
C16, C17	470 $\mu$ F, 63 V Electrolytic Capacitors	MCGPR63V477M13X26-RH	Multicomp
R1, R2	6.8 $\Omega$ , 1/4 W Chip Resistors	CRCW12066R80FKEA	Vishay
PCB	Rogers RO4350B, 0.020", $\epsilon_r = 3.66$	D65232	MTL

### TYPICAL CHARACTERISTICS — 1930–1995 MHz

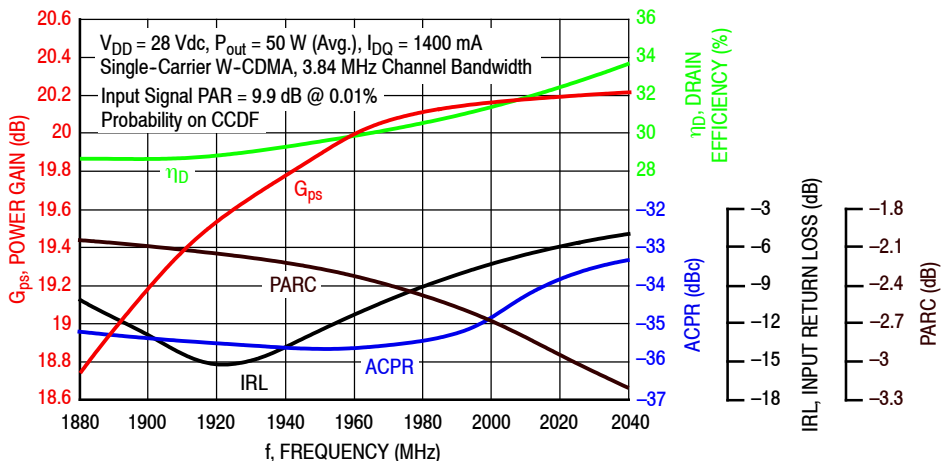


Figure 17. Single-Carrier Output Peak-to-Average Ratio Compression (PARC) Broadband Performance @  $P_{out} = 50$  Watts Avg.

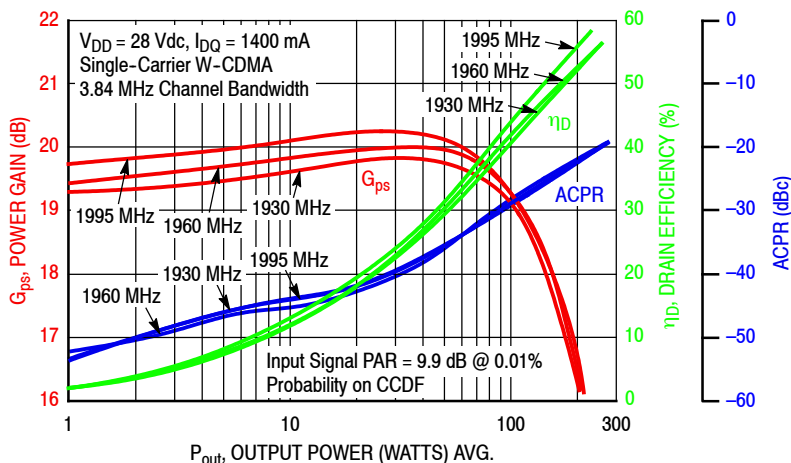


Figure 18. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power

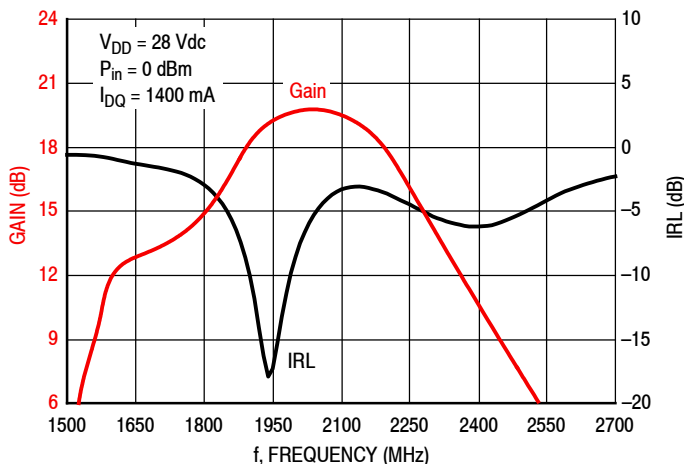


Figure 19. Broadband Frequency Response

**Table 10. Load Pull Performance — Maximum Power Tuning**

$V_{DD} = 28$  Vdc,  $I_{DQ} = 1381$  mA, Pulsed CW, 10  $\mu$ sec(on), 10% Duty Cycle

f (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{in}$ ( $\Omega$ )	Max Output Power					
			P1dB					
			$Z_{load}^{(1)}$ ( $\Omega$ )	Gain (dB)	(dBm)	(W)	$\eta_D$ (%)	AM/PM ( $^\circ$ )
1930	2.23 – j3.67	1.79 + j3.26	1.19 – j2.45	19.2	54.7	293	57.0	–15
1960	3.09 – j3.76	2.52 + j3.62	1.22 – j2.50	19.4	54.5	283	55.4	–15
1995	4.33 – j3.32	4.02 + j3.82	1.23 – j2.52	19.6	54.6	291	57.2	–14

f (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{in}$ ( $\Omega$ )	Max Output Power					
			P3dB					
			$Z_{load}^{(2)}$ ( $\Omega$ )	Gain (dB)	(dBm)	(W)	$\eta_D$ (%)	AM/PM ( $^\circ$ )
1930	2.23 – j3.67	1.80 + j3.44	1.26 – j2.62	17.0	55.5	352	58.8	–20
1960	3.09 – j3.76	2.61 + j3.86	1.31 – j2.67	17.2	55.3	339	57.0	–20
1995	4.33 – j3.32	4.29 + j4.05	1.35 – j2.70	17.4	55.4	350	59.2	–19

(1) Load impedance for optimum P1dB power.

(2) Load impedance for optimum P3dB power.

$Z_{source}$  = Measured impedance presented to the input of the device at the package reference plane.

$Z_{in}$  = Impedance as measured from gate contact to ground.

$Z_{load}$  = Measured impedance presented to the output of the device at the package reference plane.

**Table 11. Load Pull Performance — Maximum Efficiency Tuning**

$V_{DD} = 28$  Vdc,  $I_{DQ} = 1381$  mA, Pulsed CW, 10  $\mu$ sec(on), 10% Duty Cycle

f (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{in}$ ( $\Omega$ )	Max Drain Efficiency					
			P1dB					
			$Z_{load}^{(1)}$ ( $\Omega$ )	Gain (dB)	(dBm)	(W)	$\eta_D$ (%)	AM/PM ( $^\circ$ )
1930	2.23 – j3.67	1.92 + j3.39	1.68 – j1.31	21.6	53.1	206	66.7	–21
1960	3.09 – j3.76	2.77 + j3.69	1.66 – j1.25	21.9	52.8	189	64.7	–21
1995	4.33 – j3.32	4.40 + j3.80	1.48 – j1.47	21.8	53.3	215	67.0	–20

f (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{in}$ ( $\Omega$ )	Max Drain Efficiency					
			P3dB					
			$Z_{load}^{(2)}$ ( $\Omega$ )	Gain (dB)	(dBm)	(W)	$\eta_D$ (%)	AM/PM ( $^\circ$ )
1930	2.23 – j3.67	1.86 + j3.53	1.67 – j1.51	19.4	54.2	261	69.7	–27
1960	3.09 – j3.76	2.85 + j3.93	1.66 – j1.28	19.9	53.6	226	67.6	–29
1995	4.33 – j3.32	4.59 + j4.05	1.52 – j1.62	19.6	54.3	269	70.2	–27

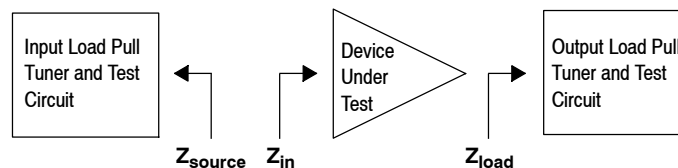
(1) Load impedance for optimum P1dB efficiency.

(2) Load impedance for optimum P3dB efficiency.

$Z_{source}$  = Measured impedance presented to the input of the device at the package reference plane.

$Z_{in}$  = Impedance as measured from gate contact to ground.

$Z_{load}$  = Measured impedance presented to the output of the device at the package reference plane.



## P1dB - TYPICAL LOAD PULL CONTOURS — 1960 MHz

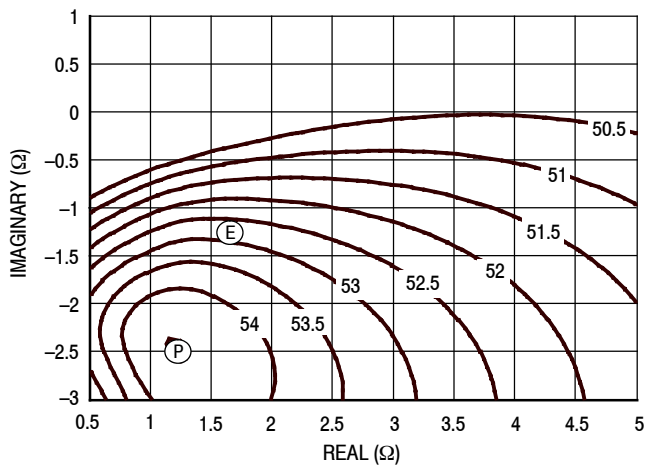


Figure 20. P1dB Load Pull Output Power Contours (dBm)

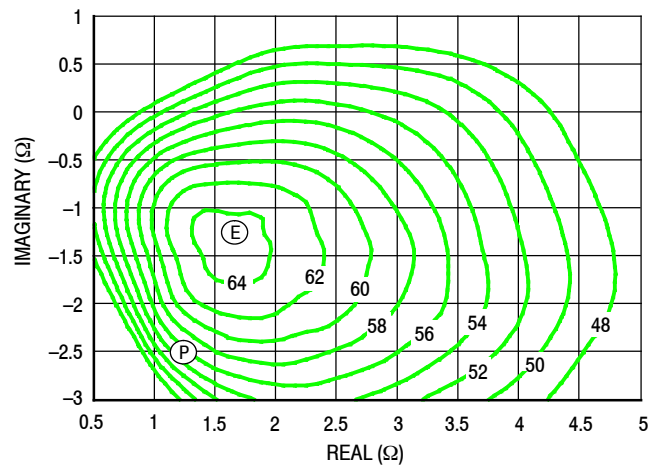


Figure 21. P1dB Load Pull Efficiency Contours (%)

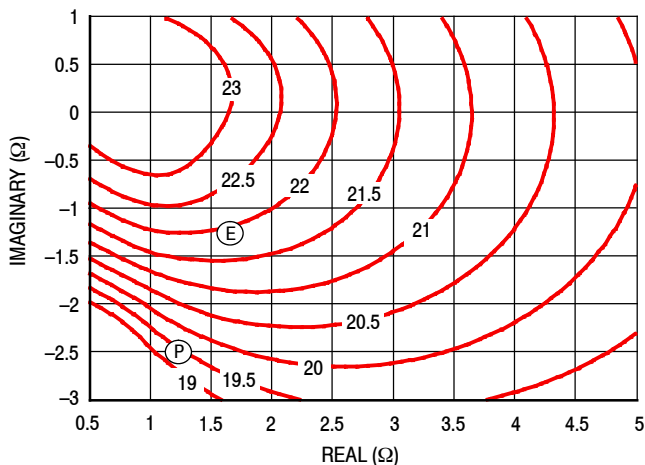


Figure 22. P1dB Load Pull Gain Contours (dB)

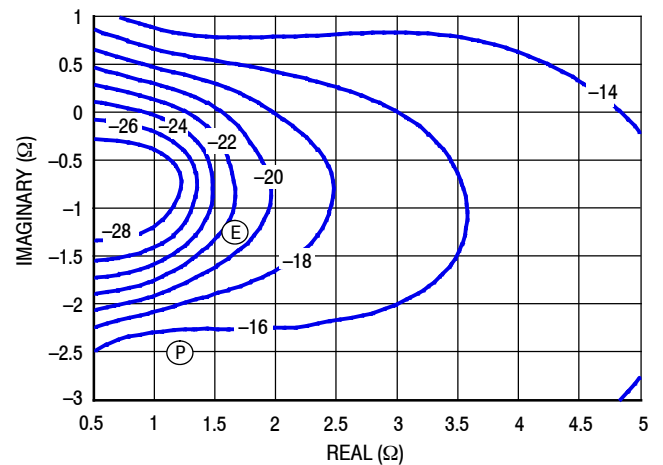


Figure 23. P1dB Load Pull AM/PM Contours (°)

**NOTE:** (P) = Maximum Output Power  
 (E) = Maximum Drain Efficiency

- Gain
- Drain Efficiency
- Linearity
- Output Power

## P3dB – TYPICAL LOAD PULL CONTOURS — 1960 MHz

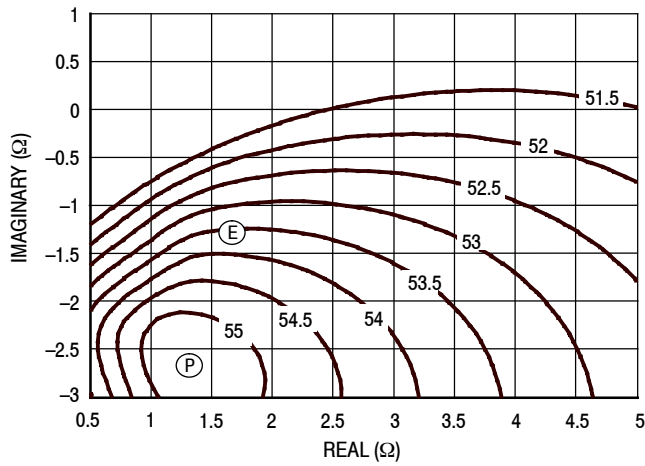


Figure 24. P3dB Load Pull Output Power Contours (dBm)

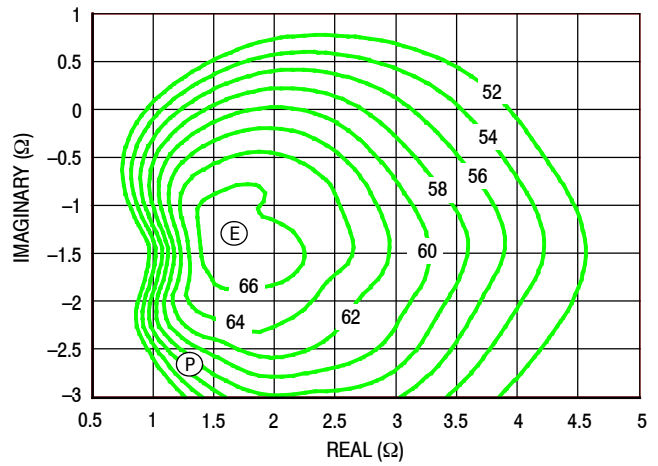


Figure 25. P3dB Load Pull Efficiency Contours (%)

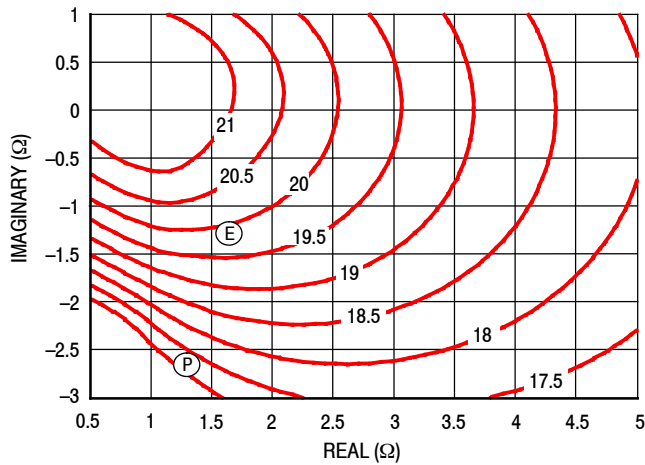


Figure 26. P3dB Load Pull Gain Contours (dB)

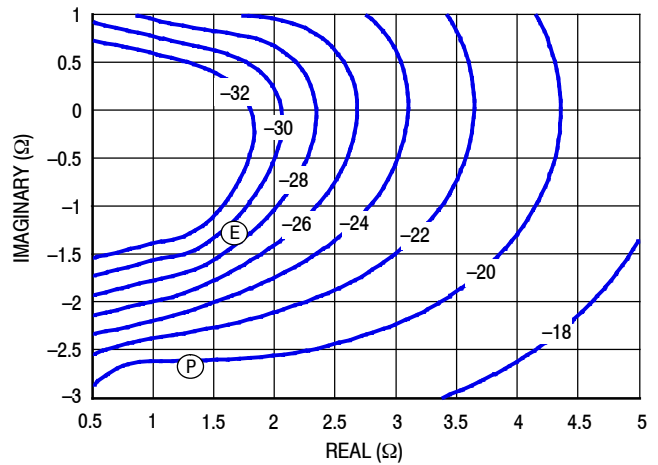
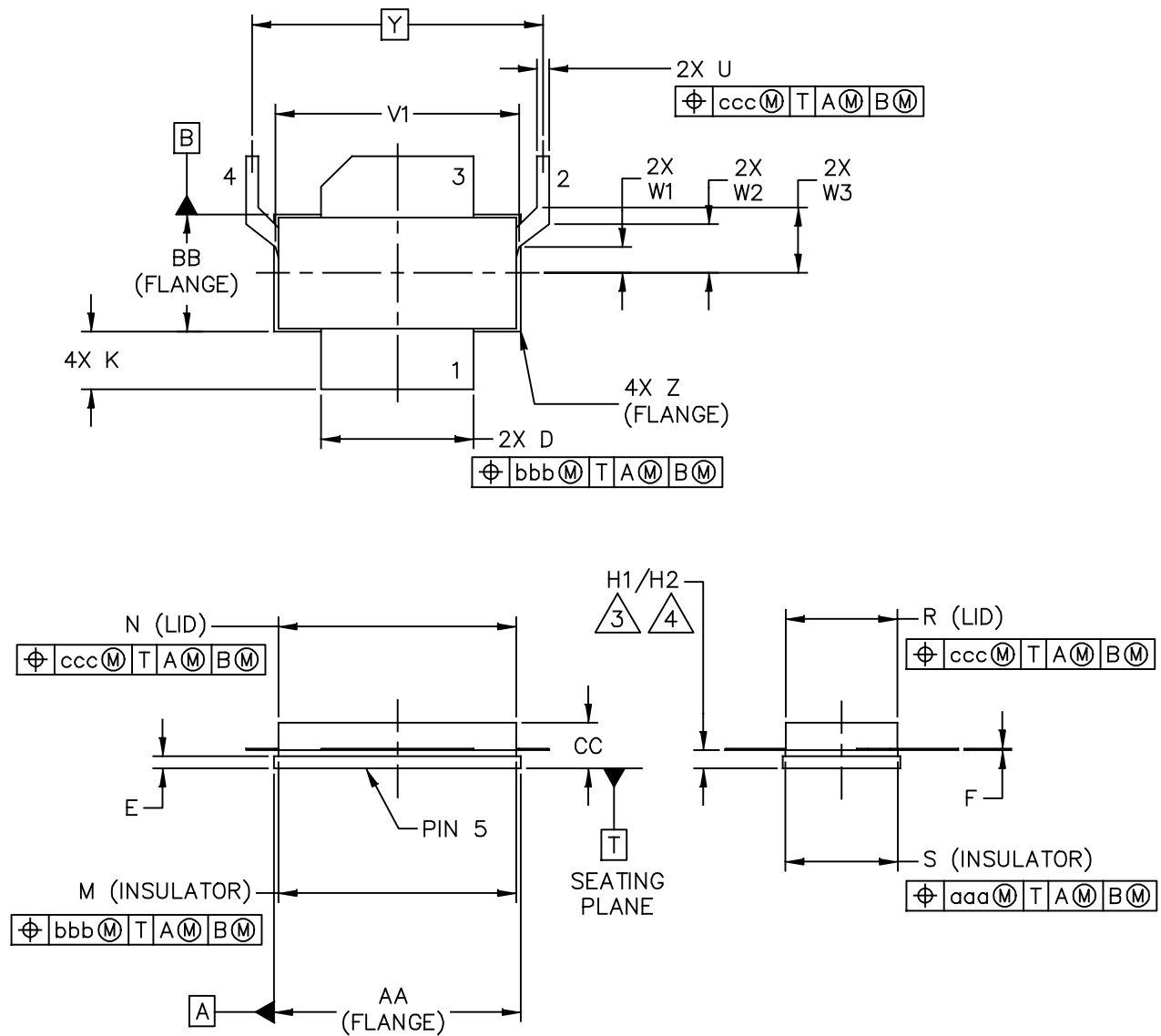


Figure 27. P3dB Load Pull AM/PM Contours (°)

**NOTE:** (P) = Maximum Output Power  
(E) = Maximum Drain Efficiency

- Gain
- Drain Efficiency
- Linearity
- Output Power

## PACKAGE DIMENSIONS



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TITLE:  <div style="text-align: center; font-size: 1.2em;">NI-780S-2L2L</div>		DOCUMENT NO: 98ASA00517D      REV: C STANDARD: NON-JEDEC SOT1785-1                              16 MAR 2016

NOTES:

1. CONTROLLING DIMENSION: INCH.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.

3. DIMENSIONS H1 AND H2 ARE MEASURED .030 INCH (0.762 MM) AWAY FROM FLANGE TO CLEAR THE EPOXY FLOW OUT PARALLEL TO DATUM B. H1 APPLIES TO PINS 1 & 3. H2 APPLIES TO PINS 2 & 4.

4. TOLERANCE OF DIMENSION H2 IS TENTATIVE AND COULD CHANGE ONCE SUFFICIENT MANUFACTURING DATA IS AVAILABLE.

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
AA	.805	.815	20.45	20.70	R	.365	.375	9.27	9.53
BB	.380	.390	9.65	9.91	S	.365	.375	9.27	9.53
CC	.125	.170	3.18	4.32	U	.035	.045	0.89	1.14
D	.495	.505	12.57	12.83	V1	.795	.805	20.19	20.45
E	.035	.045	0.89	1.14	W1	.080	.090	2.03	2.29
F	.004	.007	0.10	0.18	W2	.155	.165	3.94	4.19
H1	.057	.067	1.45	1.70	W3	.210	.220	5.33	5.59
H2	.054	.070	1.37	1.78	Y	.956 BSC		24.28 BSC	
K	.170	.210	4.32	5.33	Z	R.000	R.040	R0.00	R1.02
M	.774	.786	19.66	19.96	aaa	.005		0.13	
N	.772	.788	19.61	20.02	bbb	.010		0.25	
					ccc	.015		0.38	
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TITLE:  NI-780S-2L2L					DOCUMENT NO: 98ASA00517D      REV: C				
					STANDARD: NON-JEDEC				
					SOT1785-1			16 MAR 2016	



## PRODUCT DOCUMENTATION, SOFTWARE AND TOOLS

Refer to the following resources to aid your design process.

### Application Notes

- AN1908: Solder Reflow Attach Method for High Power RF Devices in Air Cavity Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

### Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

### Software

- Electromigration MTTF Calculator
- .s2p File

### Development Tools

- Printed Circuit Boards

### To Download Resources Specific to a Given Part Number:

1. Go to <http://www.nxp.com/RF>
2. Search by part number
3. Click part number link
4. Choose the desired resource from the drop down menu

## REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Sept. 2016	<ul style="list-style-type: none"><li>• Initial release of data sheet</li></ul>

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- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
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